Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

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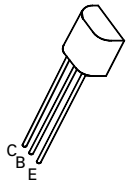
PNP SILICON PLANAR
MEDIUM POWER TRANSISTORS

ISSUE 2 – JULY 94

ZTX754
ZTX755

FEATURES

* 150 Volt V_{CEO}
* 1 Amp continuous current
* Low saturation voltage
* P_{tot}= 1 Watt



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

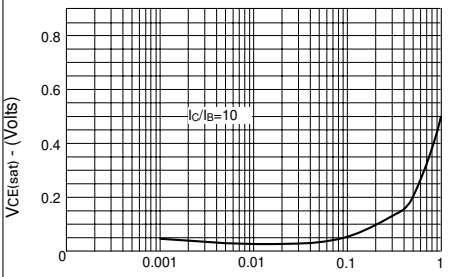
PARAMETER	SYMBOL	ZTX754	ZTX755	UNIT
Collector-Base Voltage	V_{CBO}	-125	-150	V
Collector-Emitter Voltage	V_{CEO}	-125	-150	V
Emitter-Base Voltage	V_{EBO}	-5		V
Peak Pulse Current	I_{CM}	-2		A
Continuous Collector Current	I_C	-1		A
Power Dissipation at T_{amb}=25°C	P_{tot}	1		W
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +200		°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

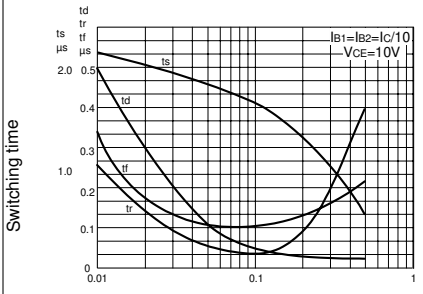
PARAMETER	SYMBOL	ZTX754		ZTX755		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-125		-150		V	I_C=-100μA, I_E=0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-125		-150		V	I_C=-10mA, I_B=0*
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		-5		V	I_E=-100μA, I_C=0
Collector Cut-Off Current	I_{CBO}		-100		 -100	nA nA	V_{CB}=-100V, I_E=0 V_{CB}=-125V, I_E=0
Emitter Cut-Off Current	I_{EBO}		-100		-100	nA	V_{EB}=-3V, I_C=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.5 -0.5		-0.5 -0.5	V V	I_C=-500mA, I_B=-50mA* I_C=-1A, I_B=-200mA*
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-1.1		-1.1	V	I_C=-500mA, I_B=-50mA*
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-1.0		-1.0	V	IC=-500mA, V_{CE}=-5V*
Static Forward Current Transfer Ratio	h_{FE}	50 50 20		50 50 20			I_C=-10mA, V_{CE}=-5V I_C=-500mA, V_{CE}=-5V* I_C=-1A, V_{CE}=-5V*
Transition Frequency	f_T	30		30		MHz	I_C=-10mA, V_{CE}=-20V f=20MHz
Output Capacitance	C_{obo}		20		20	pF	V_{CB}=-20V, f=1MHz

ZTX754
ZTX755

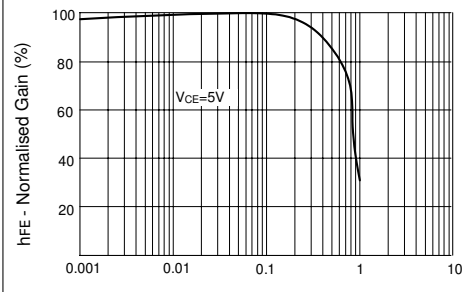
TYPICAL CHARACTERISTICS



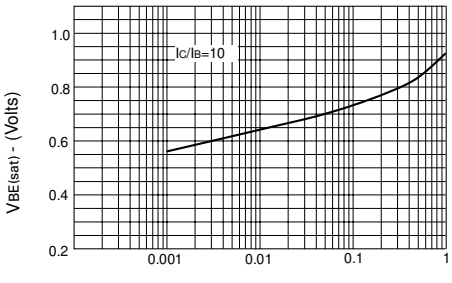
VCE(sat) v IC



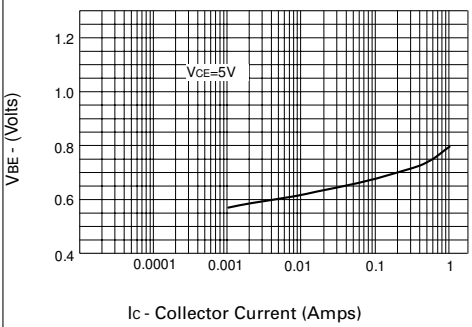
Switching Speeds



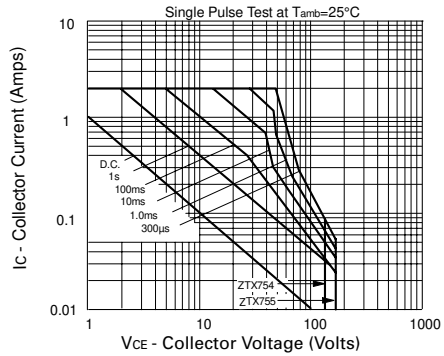
hFE v IC



VBE(sat) v IC



VBE(on) v IC



Safe Operating Area